

TOSHIBA PHOTO DARLINGTON TRANSISTOR SILICON NPN EPITAXIAL PLANAR

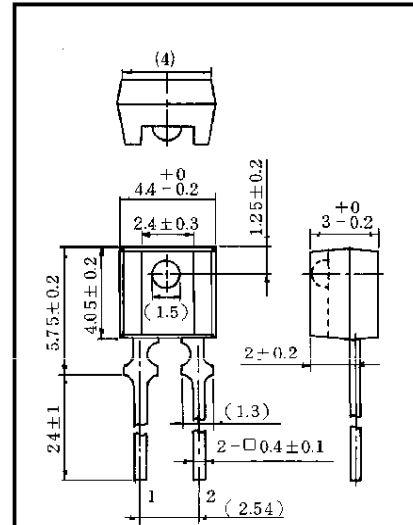
TPS617

PHOTO DARLINGTON TRANSISTOR FOR PHOTO INTERRUPTER

Unit in mm

PHOTOELECTRIC COUNTER
 POSITION DETECTION
 AUTOMATIC CONTROL UNIT

- Visible light cut type (black package)
- High sensitivity : $I_L = 1.4\text{mA}$ (TYP.)
- The same external shape as the infrared LED TLN107A, and is best suited for combination with TLN107A as a photo interrupter.
- Maximum distance when used as a photo sensor :
 TLN107A at DC drive $\approx 40\text{mm}$ When
 TPS617 $I_L \approx 350\mu\text{A}$



() : REFERENCE VALUE

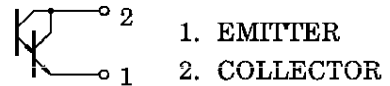
JEDEC	—
EIAJ	—
TOSHIBA	0-4B1

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Collector Voltage	V_{ECO}	5	V
Collector Current	I_C	50	mA
Collector Power Dissipation	P_C	75	mW
Collector Power Dissipation Derating (Ta > 25°C)	$\Delta P_C / ^\circ\text{C}$	-1	mW / °C
Operating Temperature Range	T_{opr}	-25~85	°C
Storage Temperature Range	T_{stg}	-40~100	°C

Weight : 0.16g (TYP.)

PIN CONNECTION



961001EAA2

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● The information contained herein is subject to change without notice.

OPTO-ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Dark Current		$I_D (I_{CEO})$	$V_{CE} = 16V, E = 0$	—	0.03	0.25	μA
Light Current (Note 1)		I_L	$V_{CE} = 3V, E = 0.1mW/cm^2$ (Note 2)	0.4	1.4	—	mA
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$V_{CE} = 0.2mA, E = 0.1mW/cm^2$ (Note 2)	—	0.9	1.2	V
Switching Time	Rise Time	t_r	$V_{CC} = 5V, I_C = 10mA$ $R_L = 100\Omega$	—	200	—	μs
	Fall Time	t_f		—	100	—	
Peak Sensitivity Wavelength		λ_P	—	—	870	—	nm
Half Value Angle		$\theta_{\frac{1}{2}}$	—	—	± 15	—	°

Note 1. I_L Classification A : 0.4~2.4mA, B : 1.7~10.2mA, C : 3mA~more

2. Color temperature = 2870°K, Standard Tungsten Lamp

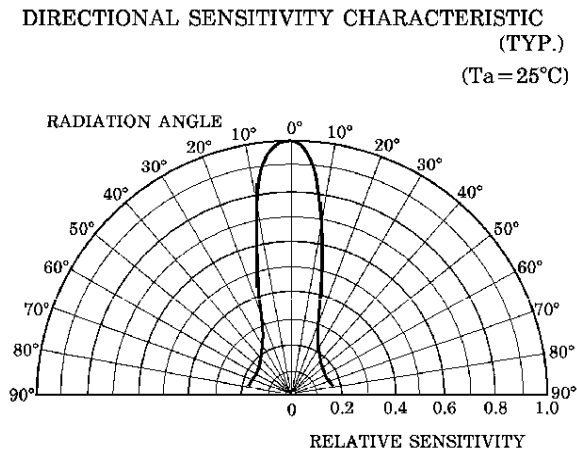
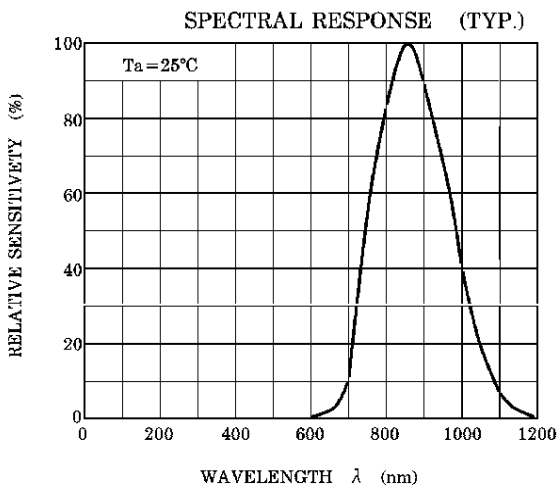
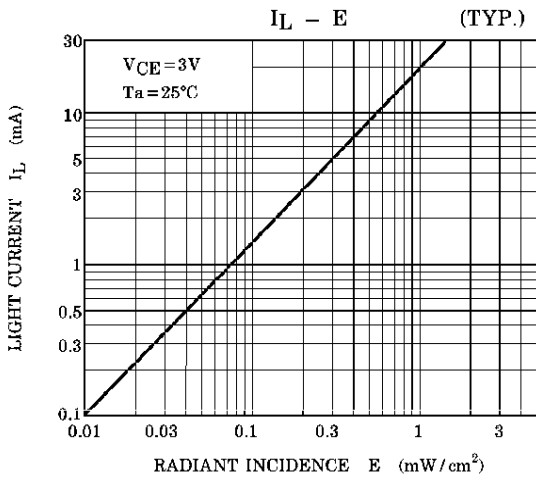
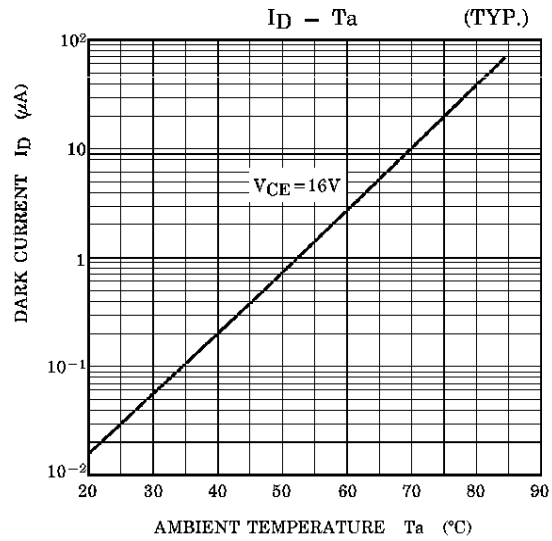
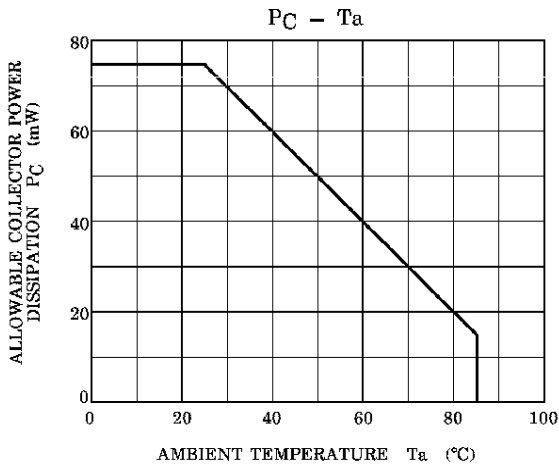
RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply Voltage	V_{CC}	—	5	16	V
Operating Temperature	T_{opr}	-25	—	75	°C

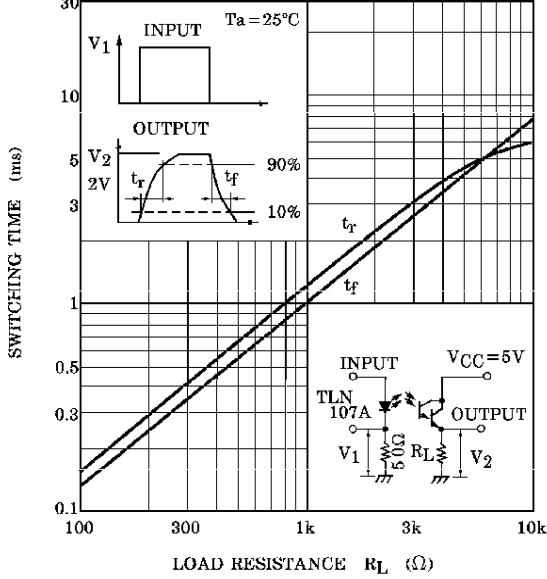
PRECAUTION

Please be careful of the followings.

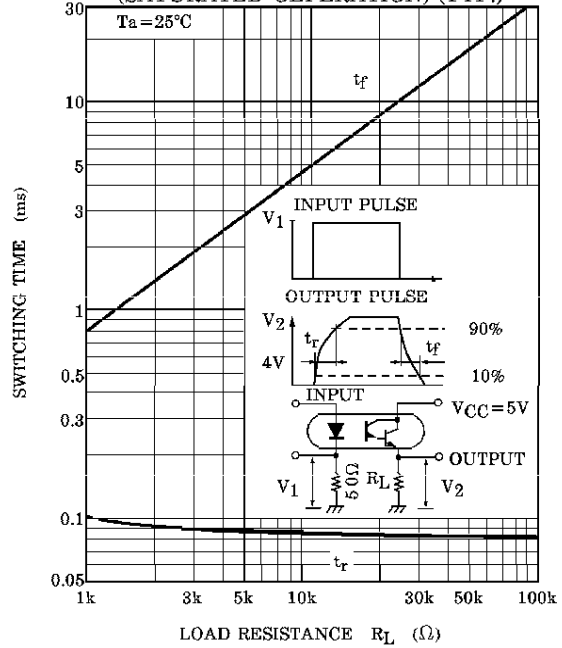
- Soldering temperature : 260°C MAX. Soldering time : 5s MAX.
(Soldering portion of lead : above 2mm from the body of the device)
- If the lead is formed, the lead should be formed at a distance of 2mm from the body of the device.
Soldering shall be performed after lead forming.



SWITCHING CHARACTERISTICS
(NON SATURATED OPERATION) (TYP.)



SWITCHING CHARACTERISTICS
(SATURATED OPERATION) (TYP.)



RELATIVE $I_L - T_a$ (TYP.)

